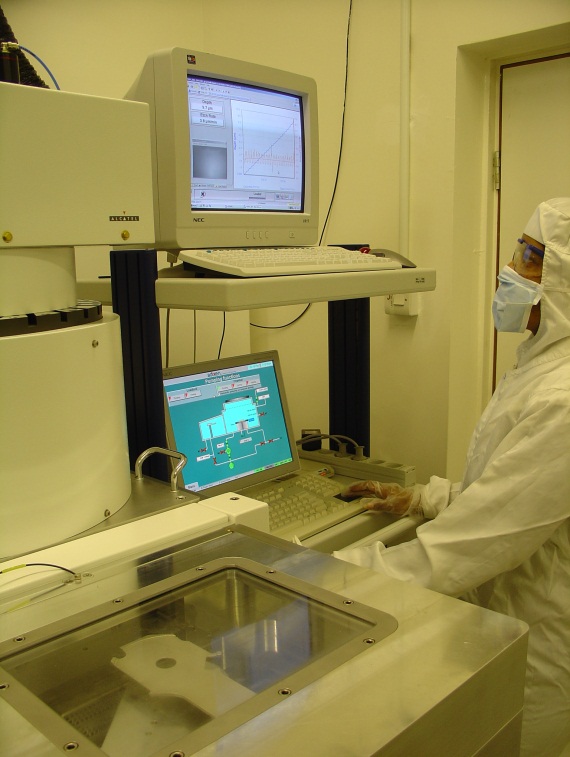
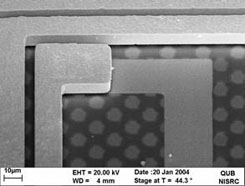
*QAMEC FOUNDRY SERVICES*



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**Thin Film Depositions & Diffusion**



|  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- |
| **Process** | **Diameter** | **Min Thickness** | **Max Thickness** | **Tolerance (+/-)** | **Notes** |
|  |  |  |  |  |  |
| Dry Oxidation | 50mm | 24nm | 200nm | 15% |  |
|  | 75mm | 24nm | 200nm | 15% |  |
|  | 100mm | 24nm | 200nm | 15% |  |
|  |  |  |  |  |  |
|  | | | | | |
| Wet Oxidation | 50mm | 100nm | 6000nm | 5% |  |
|  | 75mm | 100nm | 6000nm | 5% |  |
|  | 100mm | 100nm | 6000nm | 5% |  |
|  |  |  |  |  |  |
|  | | | | | |
| Undoped LPCVD Polysilicon | 50mm | 50nm | 2500nm | 10% | Deposition temperatures from 540C to 620C available |
|  | 100mm | 50nm | 2500nm | 10% | Deposition temperatures from 580C to 620C available |
|  | 150mm | 50nm | 2500nm | 10% | 4 wafer lay flat process |
|  | | | | | |
|  | 200mm |  |  |  | 2 wafer lay flat process |
|  |  |  |  |  |  |
|  |  |  |  |  |  |
| PECVD Silicon Dioxide/Silicon Nitride | 100mm | 50nm | - | - | Deposition Temperature:  300C for Silicon Dioxide 330C for Silicon Nitride |
|  | 150mm | 50nm | - | - |  |
|  |  |  |  |  |  |
|  |  |  |  |  |  |
|  |  |  |  |  |  |
|  |  |  |  |  |  |

**DRIE Etch Services**

|  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- |
| **Process** | **Diameter** | **MinFeature Size (CD)** | **Etch depth** | **Sidewall Angle** | **Aspect Ratio** | **Exposed etch area** | **Refill (Yes/No)** |
|  |  |  |  |  |  |  |  |
| DRIE Silicon Etch | 100mm | 2um | Contact us for engineering consultation | | | | |
|  | 150mm | 2um | Contact us for engineering consultation | | | | |
|  | 200mm | 2um | Contact us for engineering consultation | | | | |
|  | | | | | | | |
| RIE Oxide / Nitride Etch | 100mm | 2um | Contact us for engineering consultation | | | | |
|  | 150mm | 2um | Contact us for engineering consultation | | | | |
|  |  |  |  | | | | |